

# 7MBR75VN120-50

## IGBT MODULE (V series)

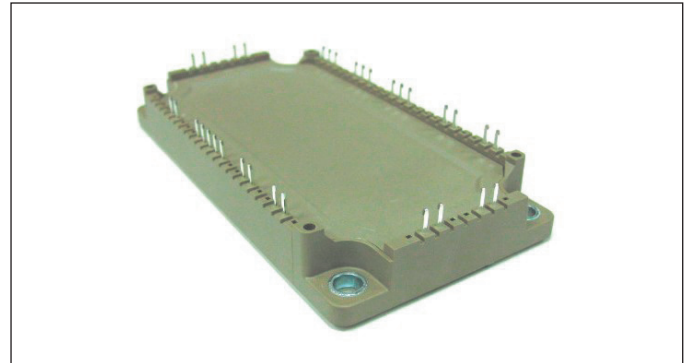
### 1200V / 75A / PIM

#### ■ Features

- Low  $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant product

#### ■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply



#### ■ Maximum Ratings and Characteristics

##### ● Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units
Inverter	Collector-Emitter voltage	$V_{CES}$			1200	V
	Gate-Emitter voltage	$V_{GES}$			$\pm 20$	V
	Collector current	$I_c$	Continuous	$T_c=80^\circ\text{C}$	75	A
		$I_{cp}$	1ms	$T_c=80^\circ\text{C}$	150	
		$-I_c$			75	
		$-I_c$ pulse	1ms			
Collector power dissipation	$P_c$	1 device		385	W	
Brake	Collector-Emitter voltage	$V_{CES}$			1200	V
	Gate-Emitter voltage	$V_{GES}$			$\pm 20$	V
	Collector current	$I_c$	Continuous	$T_c=80^\circ\text{C}$	50	A
		$I_{cp}$	1ms	$T_c=80^\circ\text{C}$	100	
	Collector power dissipation	$P_c$	1 device		280	W
	Repetitive peak reverse voltage (Diode)	$V_{RRM}$			1200	V
Converter	Repetitive peak reverse voltage	$V_{RRM}$			1600	V
	Average output current	$I_o$	50Hz/60Hz, sine wave		75	A
	Surge current (Non-Repetitive)	$I_{FSM}$	10ms, $T_j=150^\circ\text{C}$		520	A
	$I^2t$ (Non-Repetitive)	$I^2t$	half sine wave		1352	$\text{A}^2\text{s}$
Junction temperature	$T_j$	Inverter, Brake		175	$^\circ\text{C}$	
		Converter		150		
Operating junction temperature (under switching conditions)	$T_{jop}$	Inverter, Brake		150		
		Converter		150		
Case temperature	$T_c$			125		
Storage temperature	$T_{stg}$			-40 to +125		
Isolation voltage	between terminal and copper base (*1) between thermistor and others (*2)	$V_{iso}$	AC : 1min.		2500	VAC
Screw torque	Mounting (*3)	-	M5		3.5	N m

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable value : 2.5-3.5 Nm (M5)

● Electrical characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

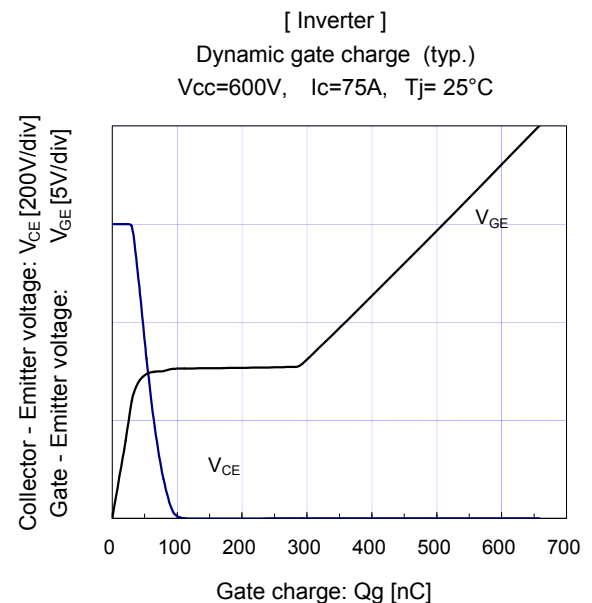
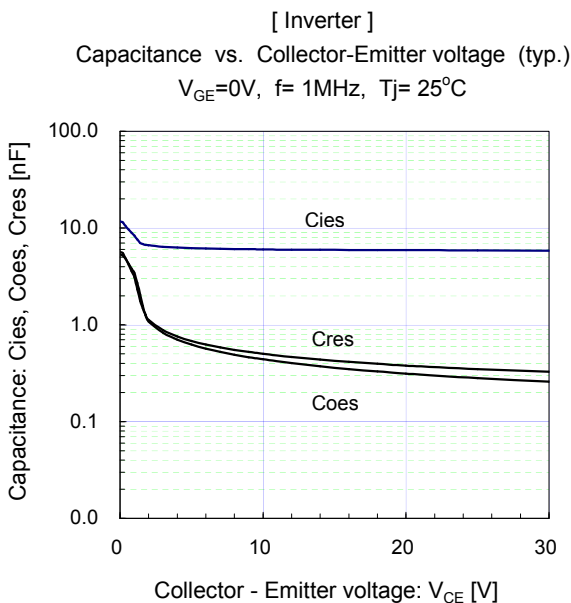
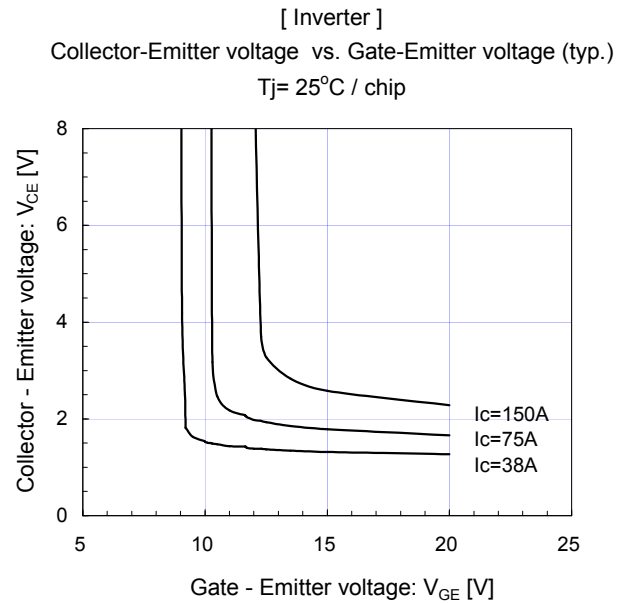
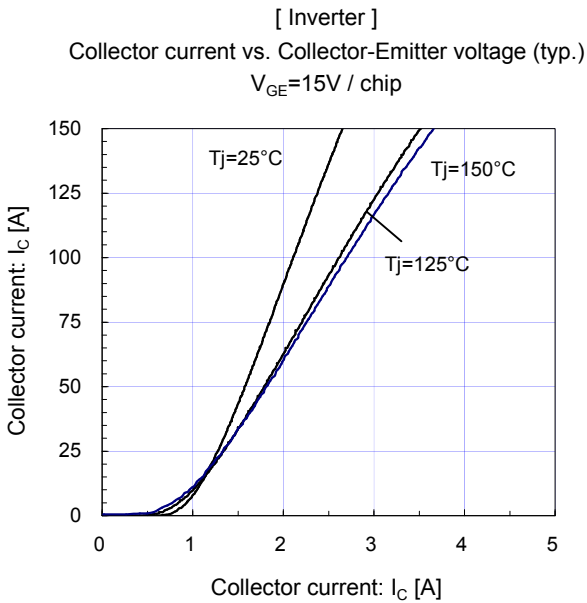
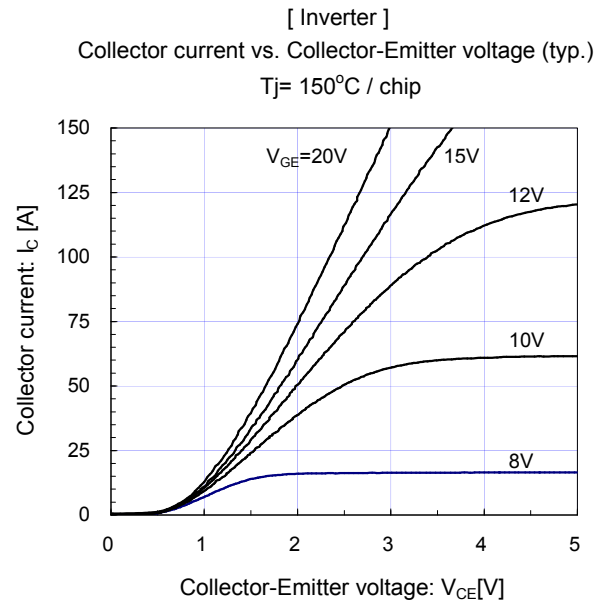
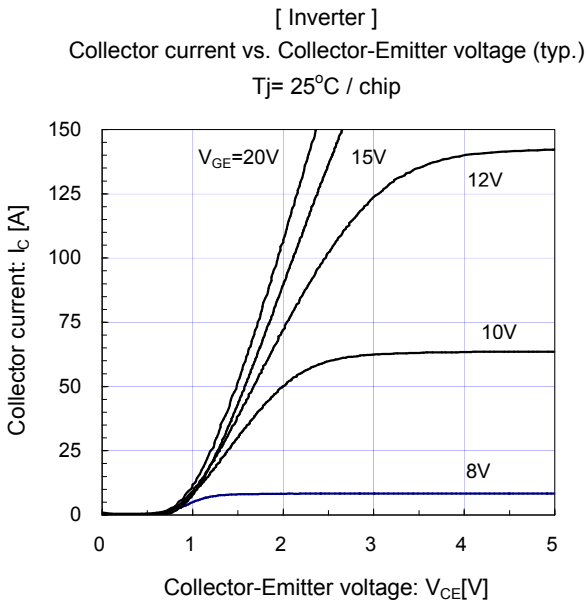
Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
Inverter	Zero gate voltage collector current	I <sub>CES</sub>	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V	-	-	1.0	mA	
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>GE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	200	nA	
	Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = 20V, I <sub>c</sub> = 75mA	6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V <sub>CE(sat)</sub> (terminal)	V <sub>GE</sub> = 15V I <sub>c</sub> = 75A	T <sub>j</sub> = 25°C	-	2.25	2.70	V
				T <sub>j</sub> = 125°C	-	2.60	-	
				T <sub>j</sub> = 150°C	-	2.65	-	
		V <sub>CE(sat)</sub> (chip)	V <sub>GE</sub> = 15V I <sub>c</sub> = 75A	T <sub>j</sub> = 25°C	-	1.85	2.30	
				T <sub>j</sub> = 125°C	-	2.20	-	
	Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz	T <sub>j</sub> = 25°C	-	6.0	-	nF
				T <sub>j</sub> = 125°C	-	6.0	-	
	Turn-on time	ton	V <sub>CC</sub> = 600V I <sub>c</sub> = 75A	T <sub>j</sub> = 25°C	-	0.39	1.20	μs
		tr		T <sub>j</sub> = 125°C	-	0.09	0.60	
		tr(i)		T <sub>j</sub> = 150°C	-	0.03	-	
	Turn-off time	toff	V <sub>GE</sub> = +15 / -15V R <sub>G</sub> = 2.2Ω	T <sub>j</sub> = 25°C	-	0.53	1.00	μs
		tf		T <sub>j</sub> = 125°C	-	0.06	0.30	
Forward on voltage	V <sub>F</sub> (terminal)	I <sub>F</sub> = 75A	T <sub>j</sub> = 25°C	-	2.10	2.55	V	
			T <sub>j</sub> = 125°C	-	2.25	-		
			T <sub>j</sub> = 150°C	-	2.20	-		
	V <sub>F</sub> (chip)	I <sub>F</sub> = 75A	T <sub>j</sub> = 25°C	-	1.70	2.15		
			T <sub>j</sub> = 125°C	-	1.85	-		
T <sub>j</sub> = 150°C	-	1.80	-					
Reverse recovery time	trr	I <sub>F</sub> = 75A	-	-	0.1	μs		
Brake	Zero gate voltage collector current	I <sub>CES</sub>	V <sub>GE</sub> = 0V V <sub>CE</sub> = 1200V	-	-	1.0	mA	
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> = 0V V <sub>GE</sub> = +20 / -20V	-	-	200	nA	
	Collector-Emitter saturation voltage	V <sub>CE(sat)</sub> (terminal)	V <sub>GE</sub> = 15V I <sub>c</sub> = 50A	T <sub>j</sub> = 25°C	-	2.10	2.55	V
				T <sub>j</sub> = 125°C	-	2.45	-	
				T <sub>j</sub> = 150°C	-	2.50	-	
		V <sub>CE(sat)</sub> (chip)	V <sub>GE</sub> = 15V I <sub>c</sub> = 50A	T <sub>j</sub> = 25°C	-	1.85	2.30	
				T <sub>j</sub> = 125°C	-	2.20	-	
	T <sub>j</sub> = 150°C	-	2.25	-				
	Turn-on time	ton	V <sub>CE</sub> = 600V I <sub>c</sub> = 50A	T <sub>j</sub> = 25°C	-	0.39	1.20	μs
		tr		T <sub>j</sub> = 125°C	-	0.09	0.60	
Turn-off time	toff	V <sub>GE</sub> = +15 / -15V R <sub>G</sub> = 15Ω	T <sub>j</sub> = 25°C	-	0.53	1.00	μs	
	tf		T <sub>j</sub> = 125°C	-	0.06	0.30		
Reverse current	IRRM	V <sub>R</sub> = 1200V	-	-	1.00	mA		
Converter	Forward on voltage	V <sub>FM</sub> (chip)	I <sub>F</sub> = 75A terminal	-	1.80	2.10	V	
			I <sub>F</sub> = 75A chip	-	1.40	-		
Thermistor	Resistance	R	T = 25°C	-	5000	-	Ω	
			T = 100°C	465	495	520		
	B value	B	T = 25 / 50°C	3305	3375	3450	K	

## ● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R <sub>th(j-c)</sub>	Inverter IGBT	-	-	0.39	°C/W
		Inverter FWD	-	-	0.55	
		Brake IGBT	-	-	0.54	
		Converter Diode	-	-	0.43	
Contact thermal resistance (1device) (*4)	R <sub>th(c-f)</sub>	with Thermal Compound	-	0.05	-	

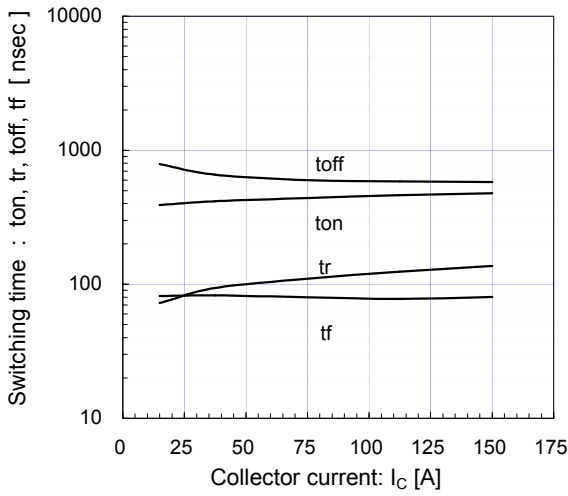
Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)



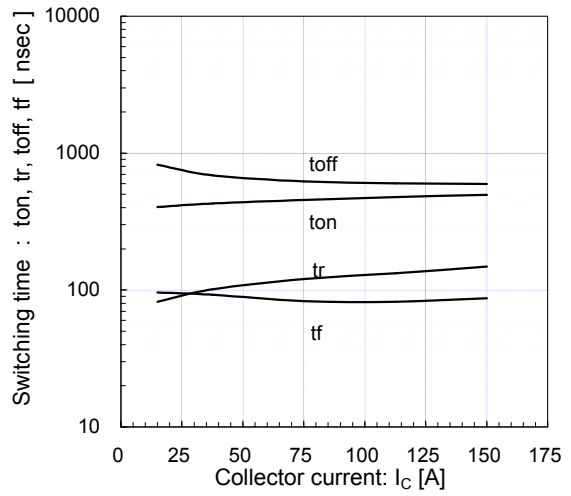
[ Inverter ]

Switching time vs. Collector current (typ.)  
 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=2.2\Omega, T_j=125^\circ C$



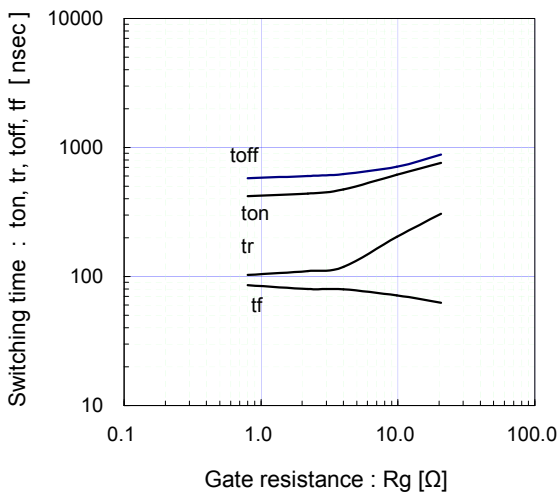
[ Inverter ]

Switching time vs. Collector current (typ.)  
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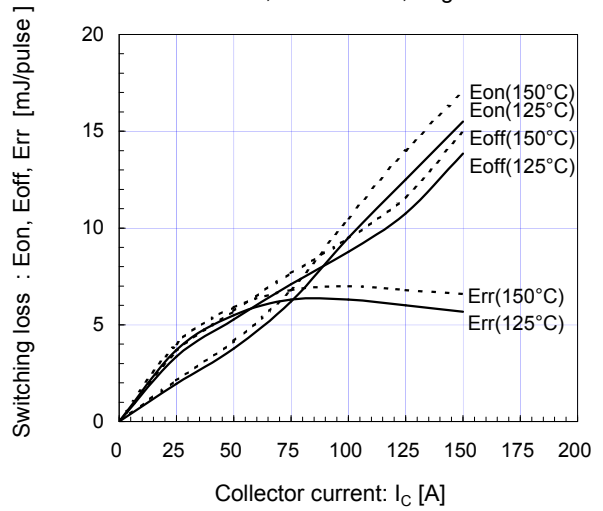
[ Inverter ]

Switching time vs. gate resistance (typ.)  
 $V_{cc}=600V, I_c=75A, V_{GE}=\pm 15V, T_j=125^\circ C$



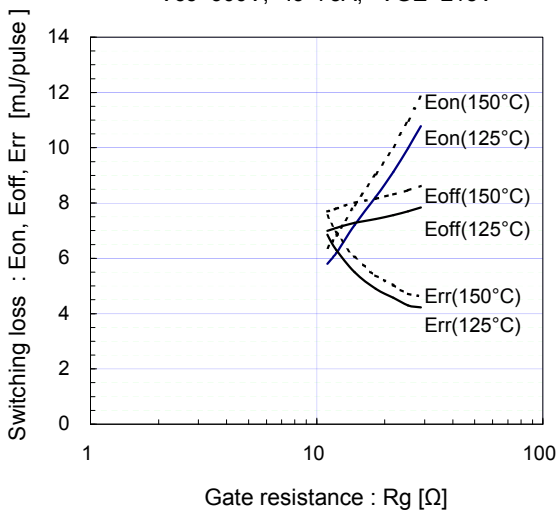
[ Inverter ] a

Switching loss vs. Collector current (typ.)  
 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=2.2\Omega$



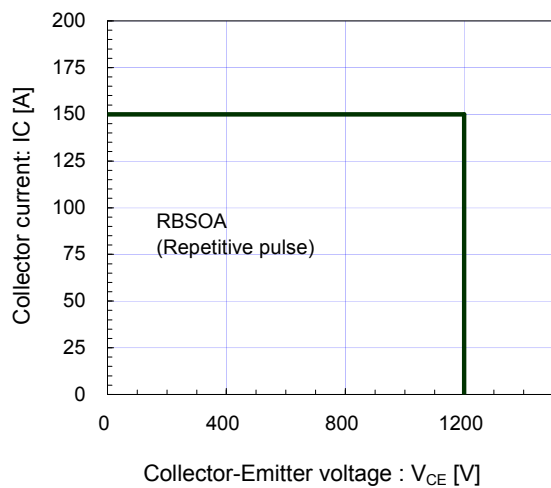
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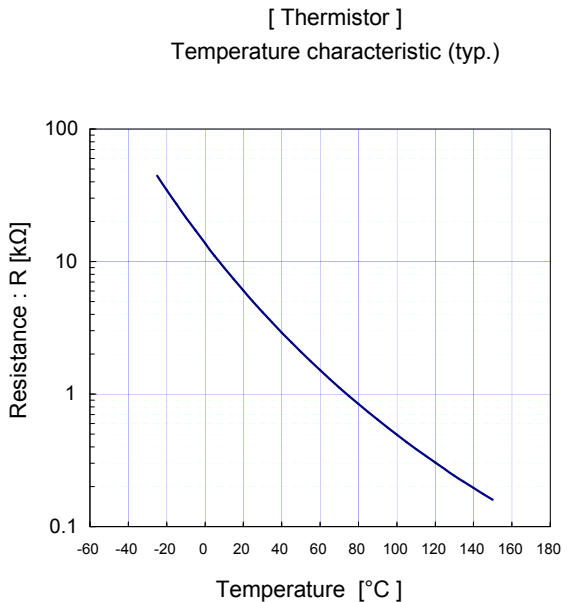
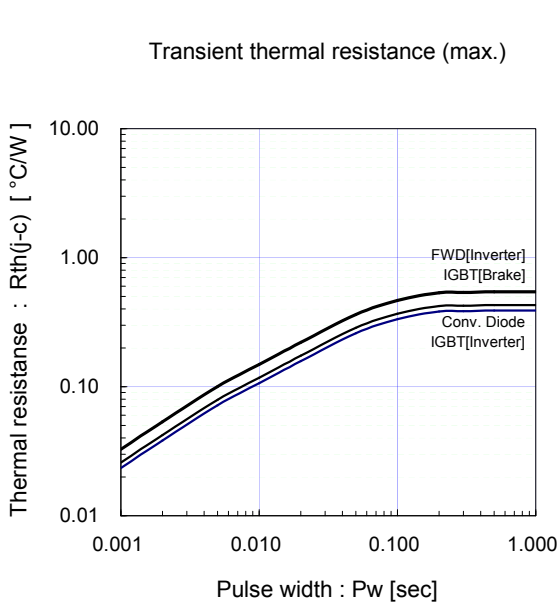
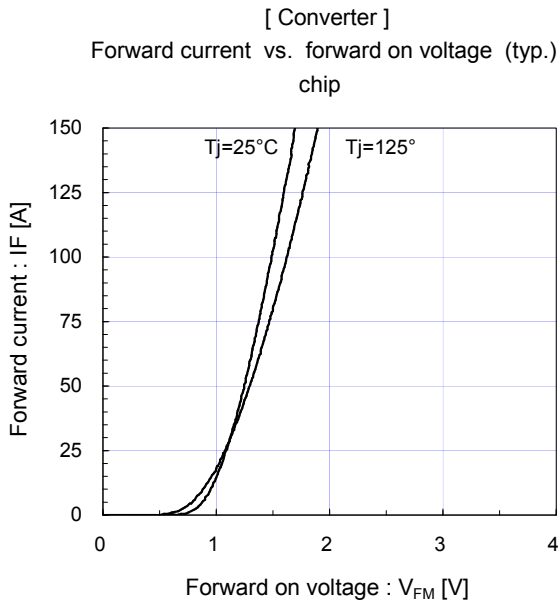
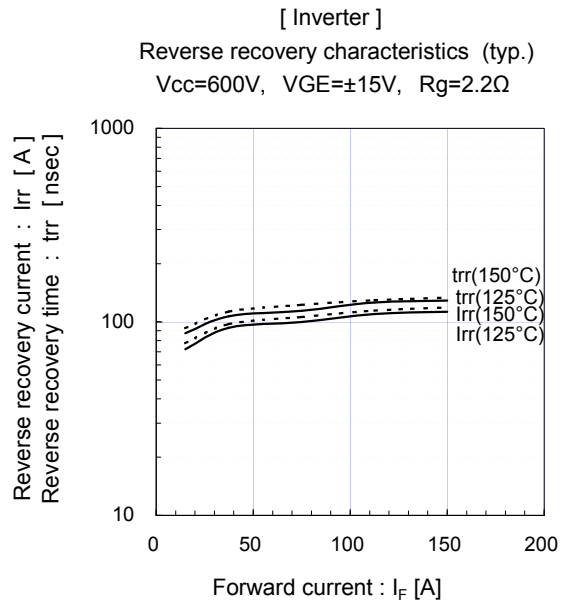
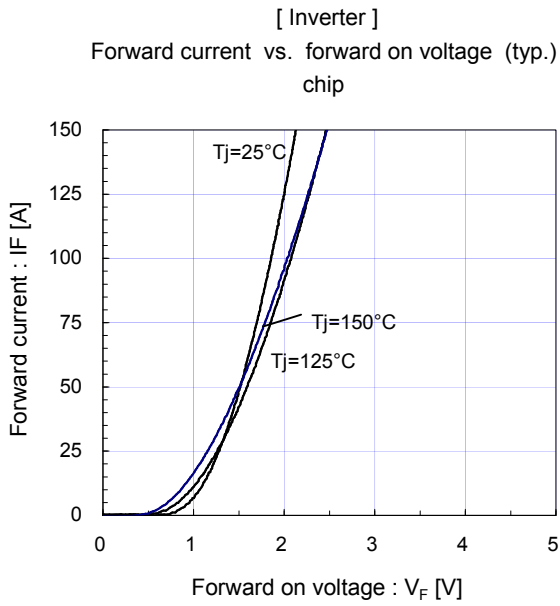
Switching loss vs. gate resistance (typ.)  
 $V_{cc}=600V, I_c=75A, V_{GE}=\pm 15V$



[ Inverter ]

Reverse bias safe operating area (max.)  
 $+V_{GE}=15V, -V_{GE} \leq 15V, R_g \geq 2.2\Omega, T_j \leq 125^\circ C$

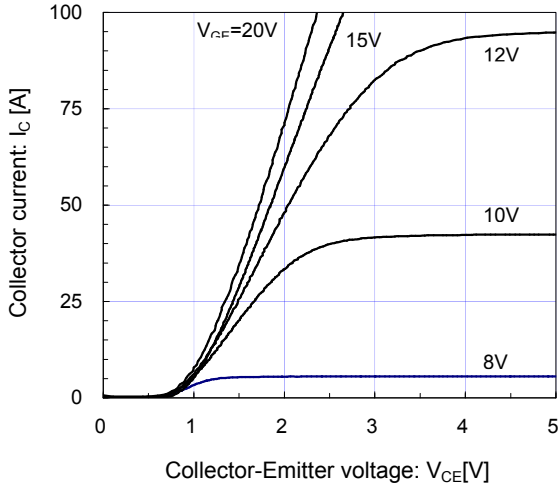




[ Brake ]

Collector current vs. Collector-Emmitter voltage (typ.)

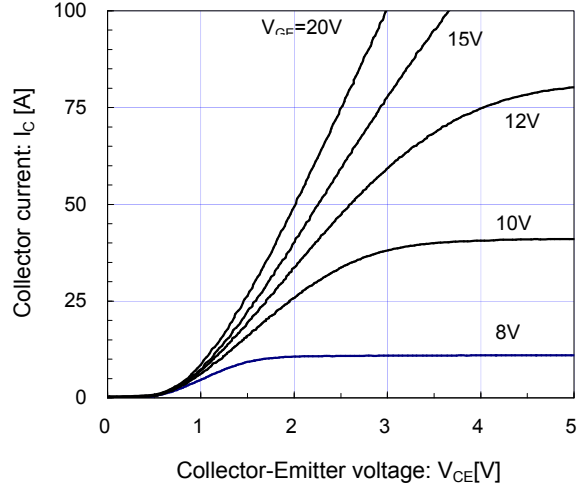
T<sub>j</sub>= 25°C / chip



[ Brake ]

Collector current vs. Collector-Emmitter voltage (typ.)

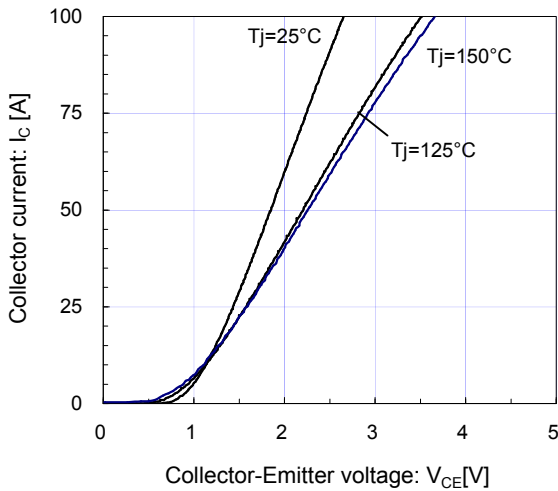
T<sub>j</sub>= 150°C / chip



[ Brake ]

Collector current vs. Collector-Emmitter voltage (typ.)

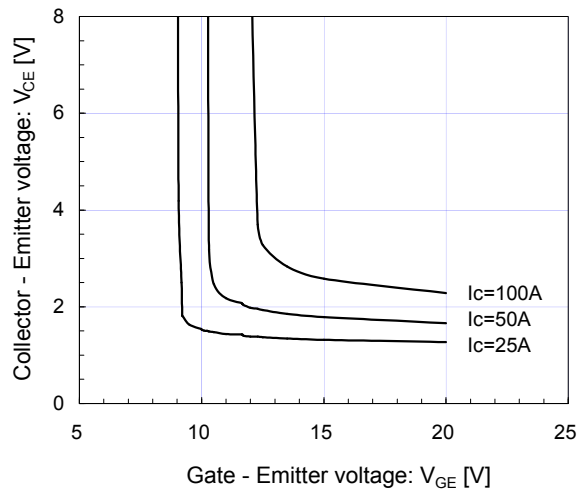
V<sub>GE</sub>=15V / chip



[ Brake ]

Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)

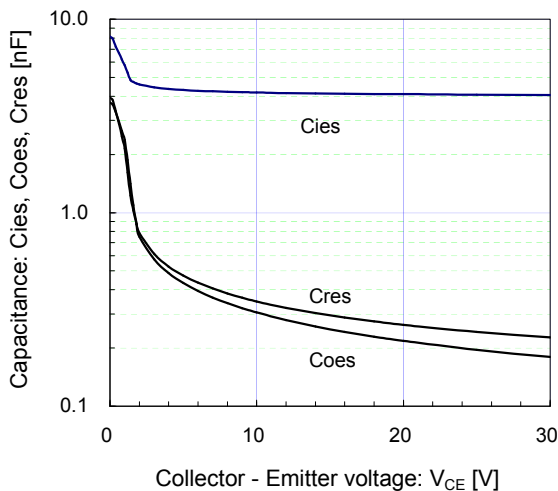
T<sub>j</sub>= 25°C / chip



[ Brake ]

Capacitance vs. Collector-Emmitter voltage (typ.)

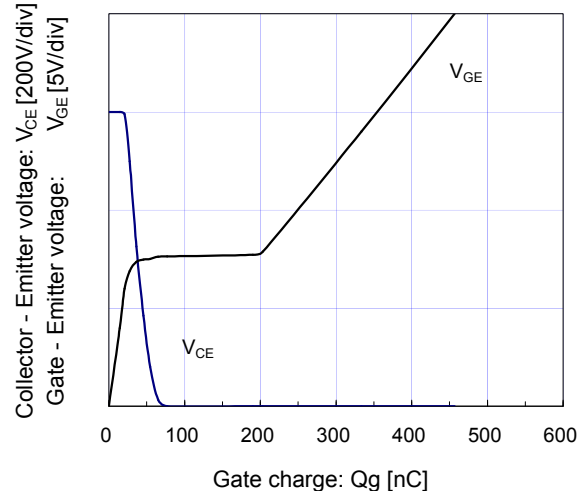
V<sub>GE</sub>=0V, f= 1MHz, T<sub>j</sub>= 25°C



[ Brake ]

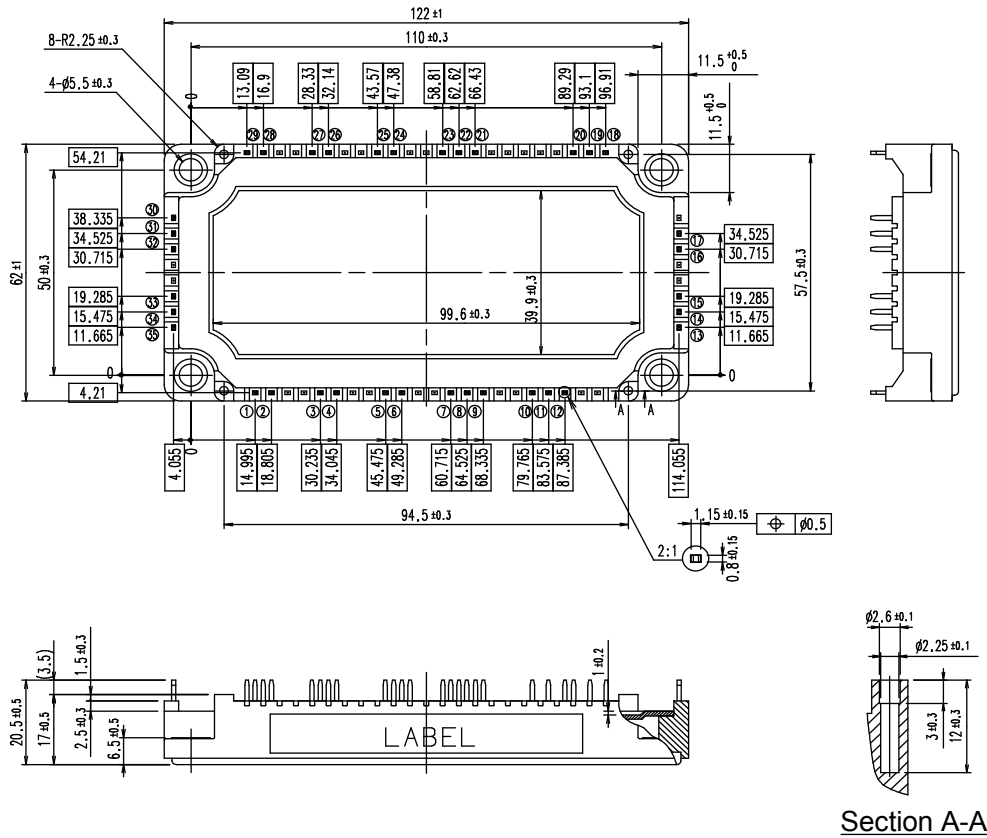
Dynamic gate charge (typ.)

V<sub>CC</sub>=600V, I<sub>c</sub>=75A, T<sub>j</sub>= 25°C

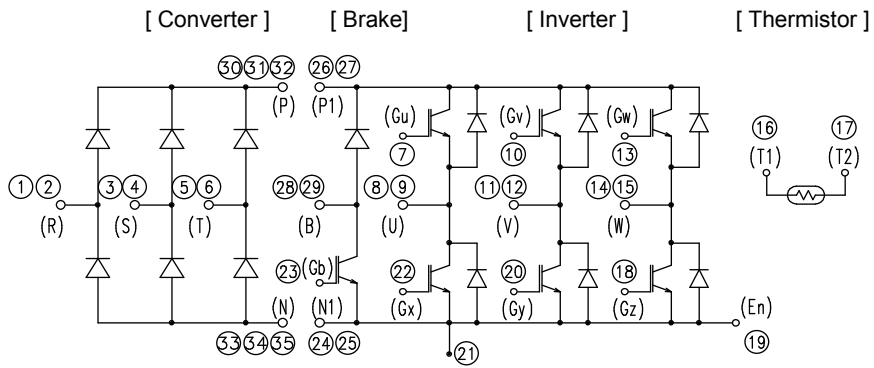


■ Outline Drawings, mm

□ shows theoretical dimension.  
 ( ) shows reference dimension.



■ Equivalent Circuit Schematic



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